Silicon PNP Power Transistors 2SB755

DESCRIPTION

·With MT-200 package
·Complement to type 2SD845
·High transition frequency
·High breakdown voltage :V_{CEO}=-150V(min)

APPLICATIONS

·For power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

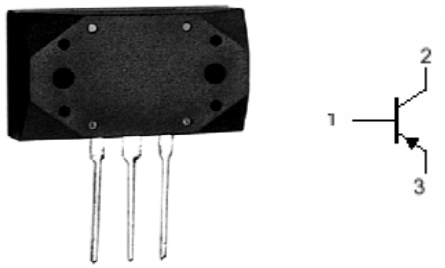

Fig.1 simplified outline (MT-200) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-12	A
I_B	Base current		-1.2	A
P_C	Collectorl power dissipation	T_C=25□	120	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-0.1A; I_B=0	-150			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-10mA; I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-5 A;I_B=-0.5 A			-2.0	V
V_{BE}	Base-emitter on voltage	I_C=-5A ; V_{CE}=-5V			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-150V; I_E=0			-50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-50	μA
h_{FE}	DC current gain	I_C=-1A ; V_{CE}=-5V	55		160	
f_T	Transition frequency	I_C=-1A ; V_{CE}=-10V		20		MHz
C_{OB}	Output capacitance	I_E=0; V_{CB}=-10V;f=1MHz		450		pF

◆ **h_{FE} classifications**

R	O
55-110	80-160

PACKAGE OUTLINE

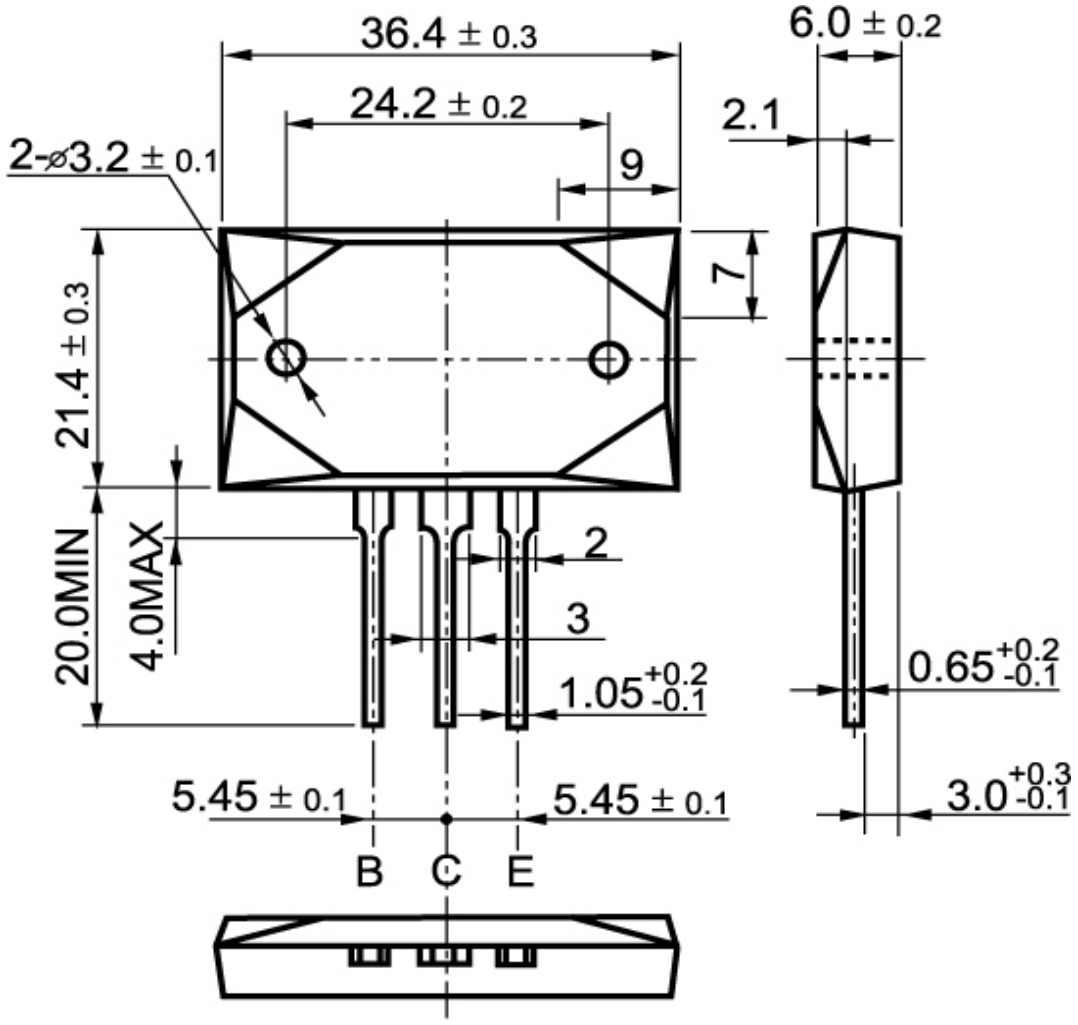

Fig.2 Outline dimensions